

## HSPICE Homework #2 of 「類比積體電路導論」

作業繳交截止日期: **Oct. 03, 2024, 18:00**

(上傳 **E3 數位平台** 繳交)

Fig. 1 is an NMOS common-source amplifier circuits with the W/L ratios of (a)  $2\mu\text{m}/0.3\mu\text{m}$  and (b)  $6\mu\text{m}/0.9\mu\text{m}$ . Perform the HSPICE simulations using device parameters of  $0.18\mu\text{m}$  CMOS technology. **Please use n\_18\_mm and p\_18\_mm.** From the simulation results,

- (1) Find the gain  $A_v = V_{out}/V_{in}$ , output DC voltage, Drain DC current,  $V_{in}$  and  $V_{out}$  capacitance, and the output resistance looking into the  $V_{out}$  node. You should use Hspice to simulate five corners and fill up the **table1**.

**Problem (2)~(3)** under TT Corner.

- (2) Calculate with the simulation parameters and compare both output resistances and gains of the circuits with different W/L between (a) and (b). Explain the reason of differences.

**Table2: Calculation Results**

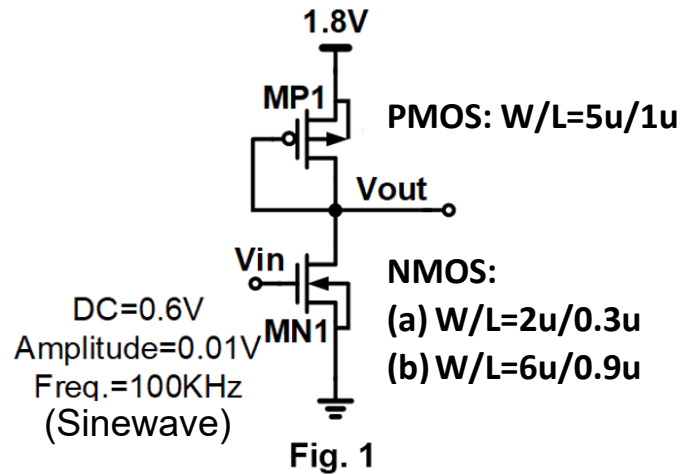
Temp.(°C)	Circuit	Rout ( $\Omega$ )	$A_v$ (V/V)
25	(a)		
25	(b)		
75	(a)		
75	(b)		

- (3) Plot the  $I_D$ - $V_{GS}$  curve and observe the variation of  $V_{th}$  and  $I_D$  by sweeping the temperatures from  $0^\circ$  to  $80^\circ$  (step= $10^\circ$ ). Explain the reason of differences. Consider the drain current  $I_D$  under the saturation region and subthreshold region.

**Table1: Simulation Results of NMOS common-source amplifier**

Corner	Temp (°C)	Circuit	Vout (V)	Ids (mA)	*DC Gain $A_v$ (V/V)	Rout ( $\Omega$ )	Cin (F)	Cout (F)
TT	25	(b)						
TT	0	(a)						
TT	25	(a)						
TT	75	(a)						
FF	25	(a)						
SS	25	(a)						
FnSp	25	(a)						
SnFp	25	(a)						

\*The DC gain is the low-frequency gain.



HSPICE\_HW2：作業需要有以下幾點：

1. HSPICE Code (截圖)
2. Simulation Result (波形繳交背景請用白色，並且波形標示和呈現要清楚)
3. 每個小題的單獨說明

**問題(1)** 填表格

**問題(2)** 計算、表格、說明

**問題(3)** 說明、波型圖

4. 以.pdf 的格式上傳
5. 檔案名稱用「Hspice\_HW2\_自己的學號」(例如：Hspice\_HW2\_0811541)，於作業繳交截止日期(發布後隔週禮拜四晚上 6 點)前，上傳到指定的 E3 數位平台繳交，遲交一周內打八折，一周後不計分。